



Japan TC Chapter of Compound Semiconductor Materials Global Technical Committee

Liaison Report

October, 2024

STANDARDS

Meeting Information

- Last meeting
 - Tuesday, May 21, 2024
 - SEMI Japan Office + OVTCCM (Hybrid)
- Next meeting
 - Thursday, December 12, 2024
 - Tokyo Big Sight, Tokyo, Japan + OVTCCM (Hybrid) in conjunction with SEMICON Japan 2024

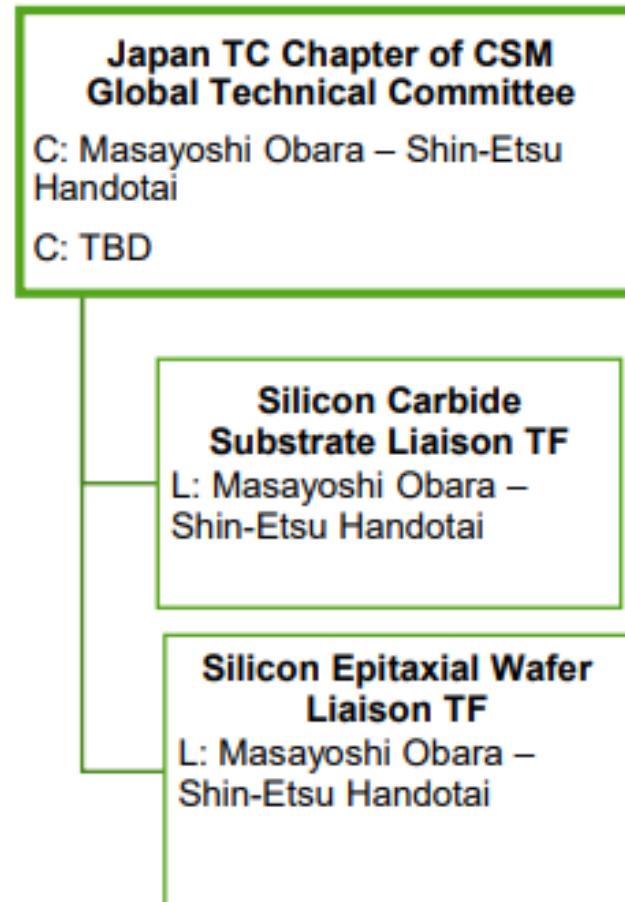
[Visit the Standards Calendar for details.](#)

TC Chapter Leadership

Co-chairs

- Masayoshi Obara (Shin-Etsu Handoutai)
 - GCS voting member

Organization Chart



Ballot Results

Doc#	Document Title	TC Chapter Action
7211	Line Item Revision to SEMI M92-0423, Specification for 4H-SiC Homoepitaxial Wafer	
LI1	Revise the test pattern in section 6.4.3.1	Failed
LI2	Revise the specification of test points coordinates in Table 2 in section 6.4.3.2	Failed
LI3	Revise the calculation formula of Tolerance in section 6.4.3.3	Passed, with editorial changes
LI4	Revise the specification of carrier concentration of Tolerance in Table 3 in section 6.4.3.4	Passed as balloted
LI5	Revise the specification of thickness of Tolerance in Table 4 in section 6.4.4.2	Passed as balloted

Note 1: **Passed** ballots and line items will be submitted to the ISC Audit & Review Subcommittee for procedural review.

Note 2: **Failed** ballots and line items were returned to the originating task forces for re-work and re-balloting or abandoning.

Activities Approved via GCS between Meetings

#	Type	SC/TF/WG	Title/Details
None			

Authorized Activities

#	Type	SC/TF/WG	Document Title/Details
None			

Note 1: SNARFs and TFOFs are available for review on the SEMI Web site at:

<http://downloads.semi.org/web/wstdsbal.nsf/TFOFSNARF>

Authorized Ballots

#	When	TF	Document Title/Details
None			

5-Year Review

Designation#	Standard Title	Action By	Assigned to
None			

Task Force Highlights

- Silicon Carbide Substrate Liaison Task Force
 - Reviewing Doc.# 6767A, New Standard: Test Method for Flatness of Silicon Carbide Wafers by Optical Interference as well as Doc.#6769B, New Standard: Test Method for Residual Stress of Silicon Carbide Wafers by Photoelastic, which are under development by the Silicon Carbide Substrate Task Force under the Compound Semiconductor Materials China TC Chapter.
 - Continue to communicate with the said Task Force to improve the draft documents.
- SiC Epitaxial Wafer Liaison Task Force
 - Will work on failed Line Items of Doc.#7211.
 - Considering to include 200.0 mm 4H-SiC epitaxial wafers in SEMI M92, Specification for 4H-SiC Homoepitaxial Wafer by submitting another SNARF.

Questions?

- For more information, please contact:
Akiko Yoshida at ayoshida@semi.org



THANK YOU

STANDARDS